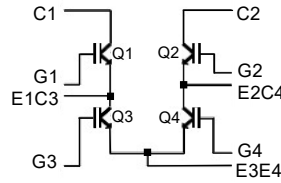


High Voltage IGBT For Capacitor Discharge Applications

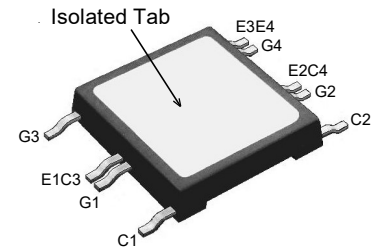
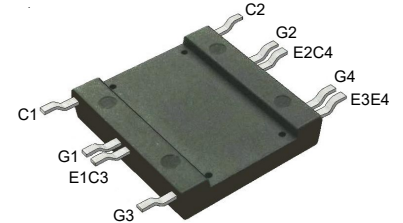
MMIX4G20N250

(Electrically Isolated Tab)

H-Bridge Configuration



$$\begin{aligned} V_{CES} &= 2500V \\ I_{C25} &= 23A \\ V_{CE(sat)} &\leq 3.1V \end{aligned}$$



G = Gate
C = Collector
E = Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	2500	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1M\Omega$	2500	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	23	A
I_{C90}	$T_C = 90^\circ\text{C}$	14	A
I_{CM}	$T_C = 25^\circ\text{C}, V_{GE} = 19V, 1ms$ 10ms	105 55	A A
SSOA	$V_{GE} = 15V, T_{VJ} = 125^\circ\text{C}, R_G = 20\Omega$	$I_{CM} = 60$	A
(RBSOA)	Clamped Inductive Load	1500	V
P_C	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ\text{C}$
F_C	Mounting Force	50..200 / 11..45	Nm/lb.in.
V_{ISOL}	50/60Hz, 1 Minute	4000	V~
Weight		8	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}, V_{GE} = 0V$ Note 2, $T_J = 125^\circ\text{C}$			10 μA 750 μA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 20A, V_{GE} = 15V, \text{ Note 1}$			3.1 V

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 4000V~ Electrical Isolation
- High Peak Current Capability
- Low Saturation Voltage
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- High Power Density
- Easy to Mount

Applications

- Capacitor Discharge
- Pulser Circuits

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 20\text{A}$, $V_{CE} = 10\text{V}$, Note 1	8	13	S
$I_{C(ON)}$	$V_{GE} = 20\text{V}$, $V_{CE} = 15\text{V}$, Note 1		190	A
C_{ies}	$V_{CE} = 15\text{V}$, $V_{GE} = 20\text{V}$, $f = 1\text{MHz}$		1190	pF
C_{oes}			53	pF
C_{res}			18	pF
Q_g	$I_C = 20\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 1000\text{V}$		53	nC
Q_{ge}			8	nC
Q_{gc}			22	nC
$t_{d(on)}$	Resistive Switching Times $I_C = 40\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}$, $R_G = 10\Omega$		57	ns
t_r			160	ns
$t_{d(off)}$			136	ns
t_f			930	ns
R_{thJC}				1.25 $^\circ\text{C/W}$
R_{thCS}		0.05		$^\circ\text{C/W}$
R_{thJA}		30		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.

Littelfuse reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

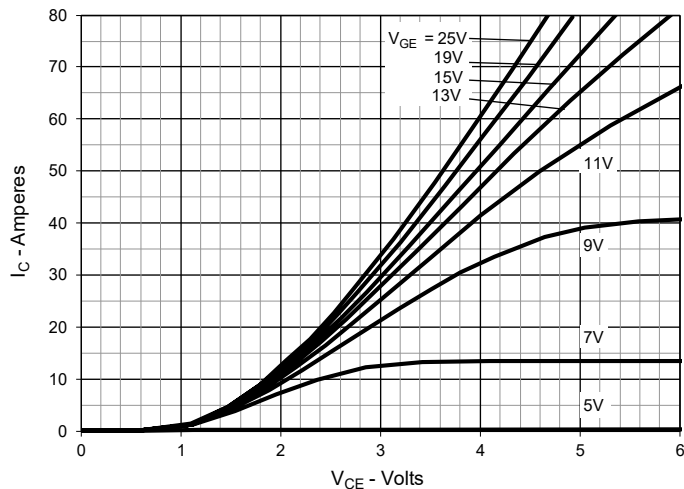


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

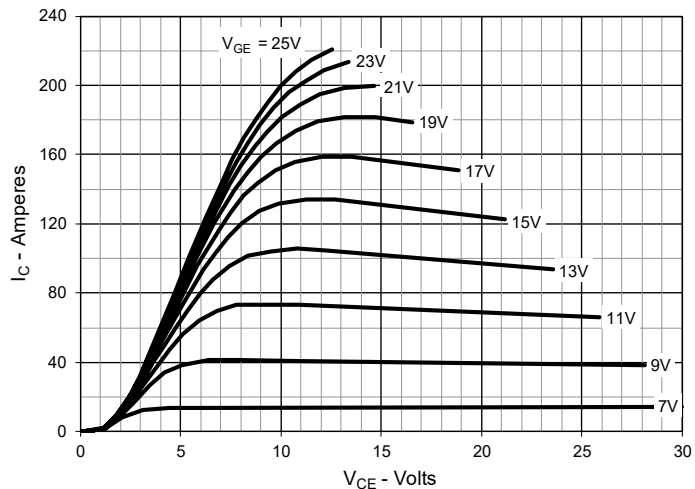


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

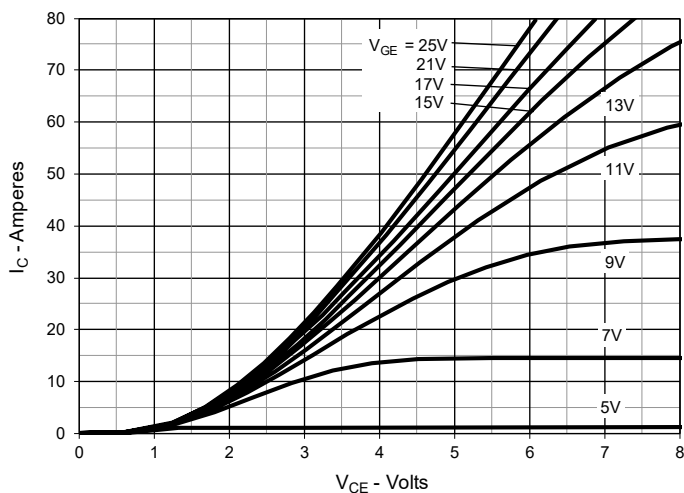


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

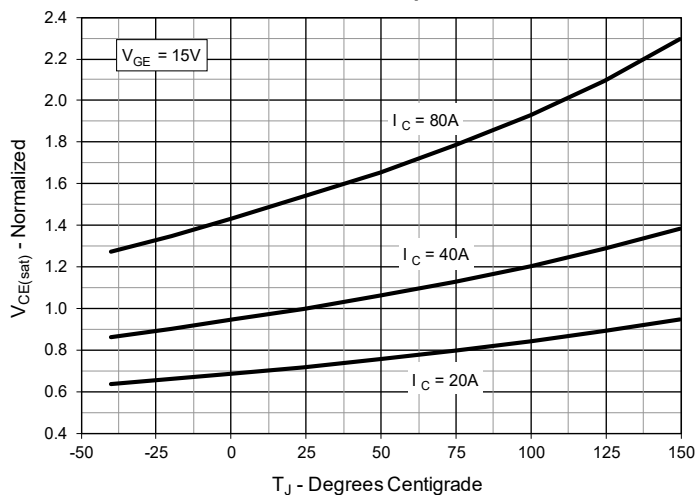


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

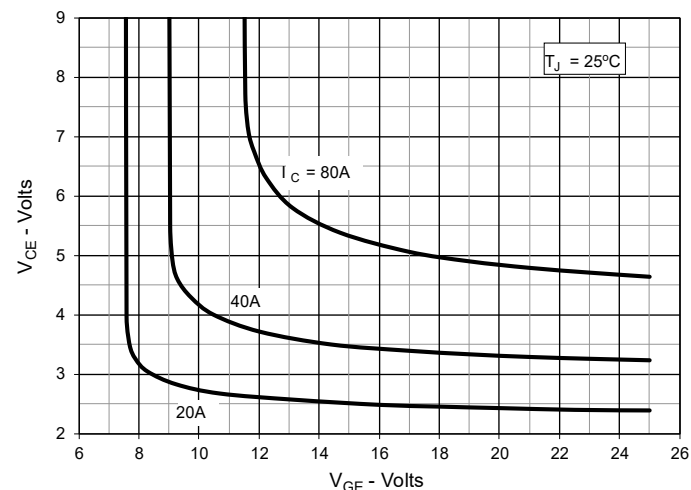


Fig. 6. Input Admittance

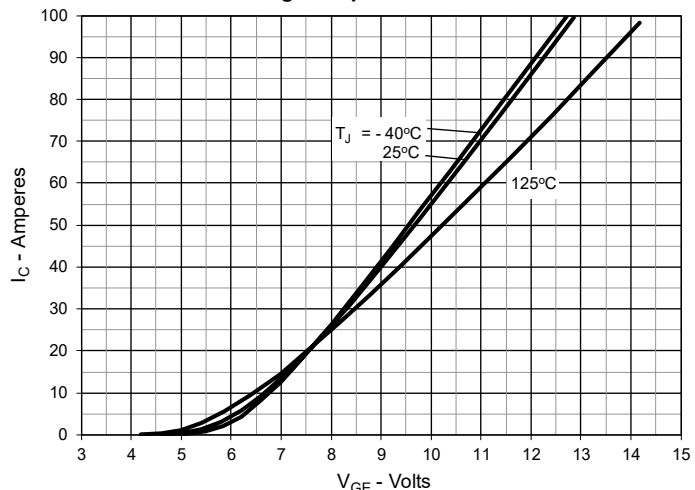


Fig. 7. Transconductance

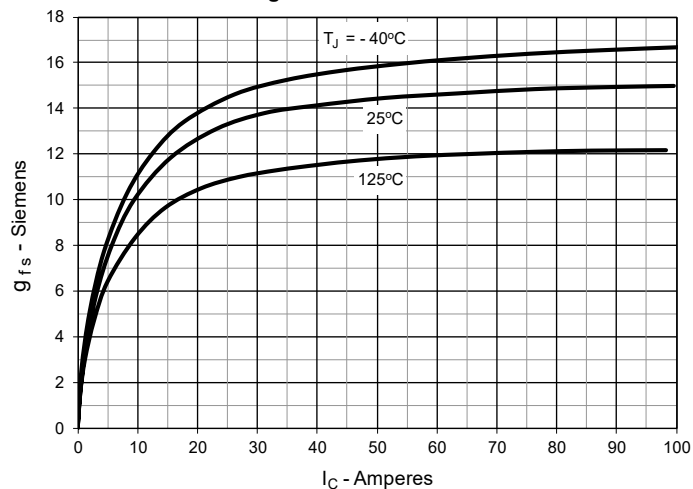


Fig. 8. Gate Charge

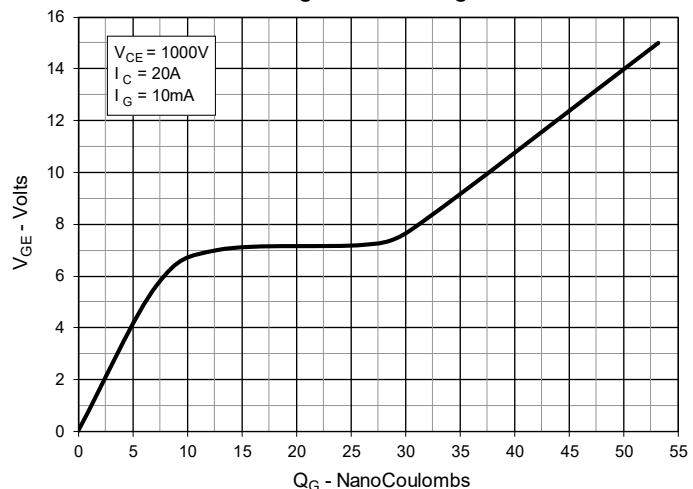


Fig. 9. Reverse-Bias Safe Operating Area

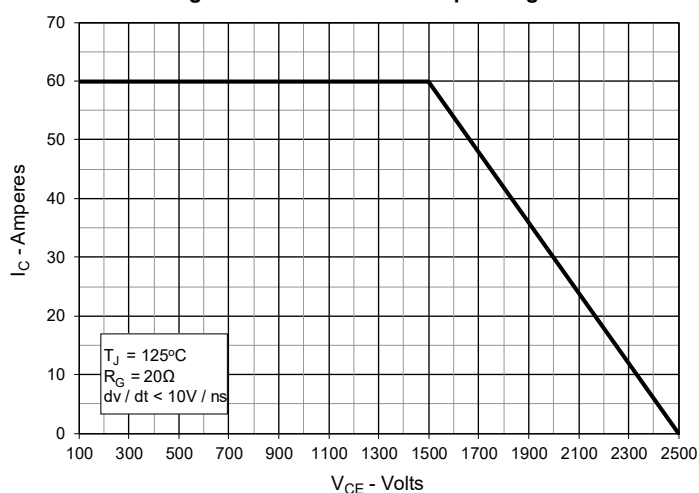


Fig. 10. Capacitance

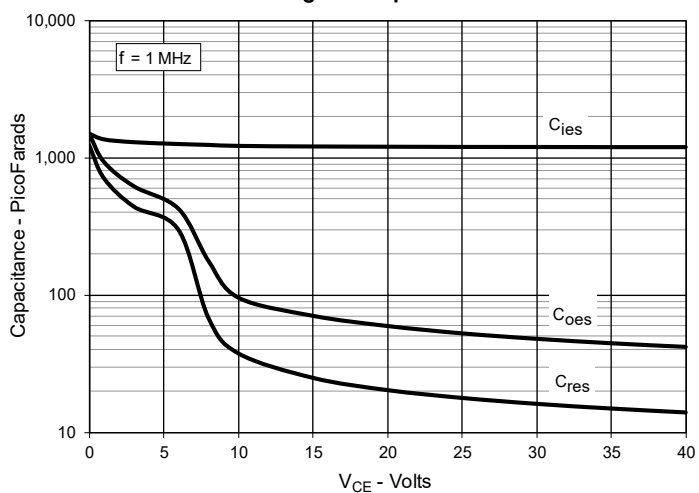


Fig. 11. Maximum Transient Thermal Impedance

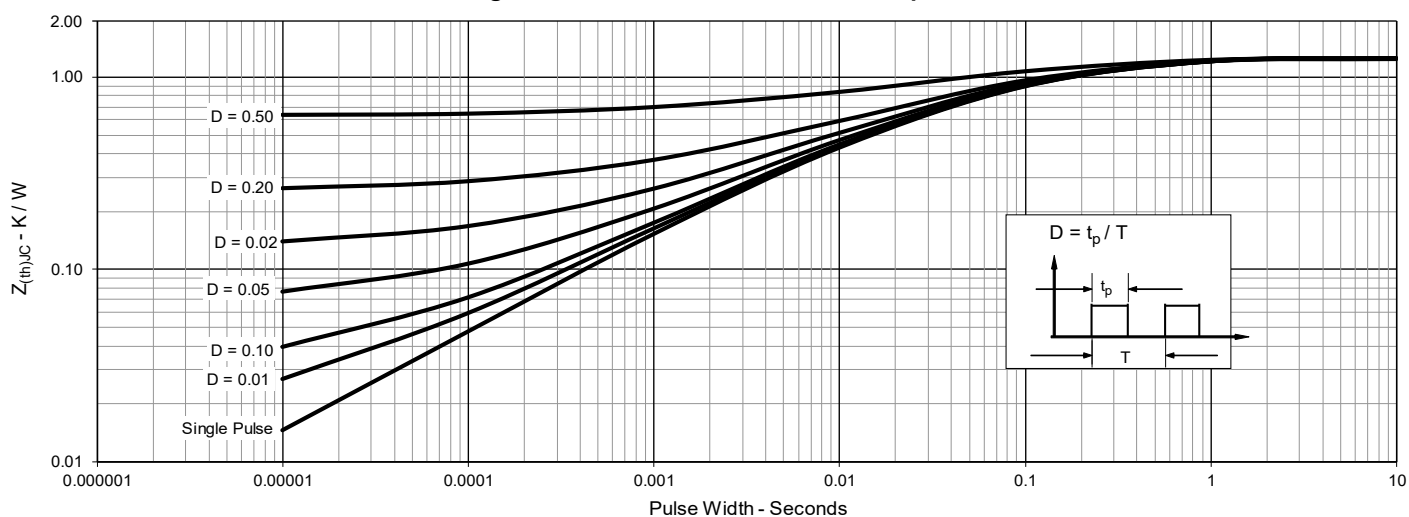


Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature

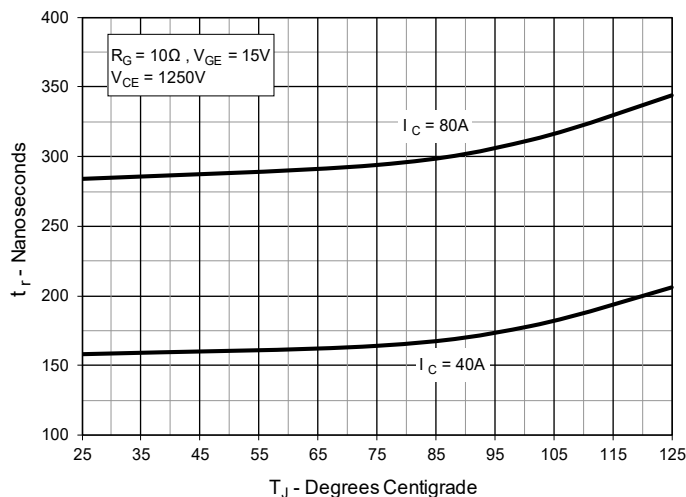


Fig. 13. Resistive Turn-on Rise Time vs. Collector Current

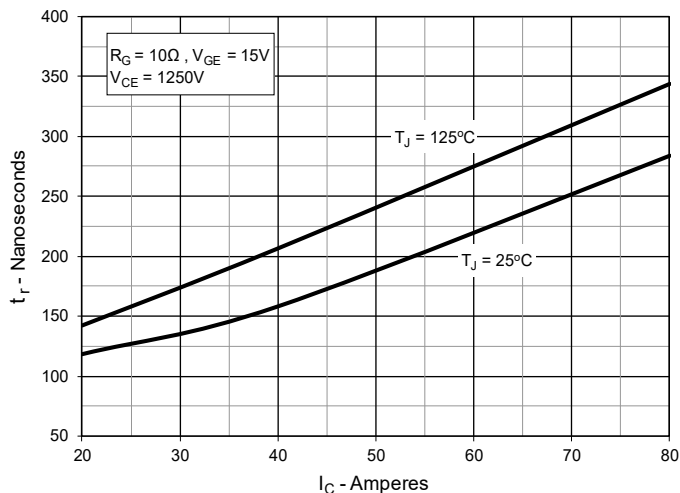


Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance

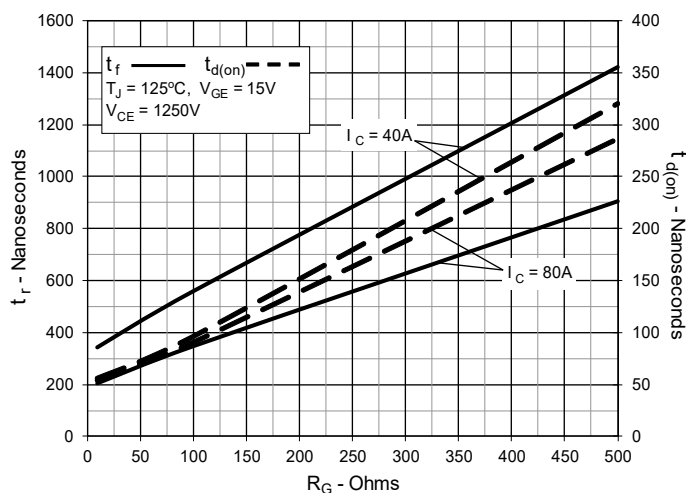


Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature

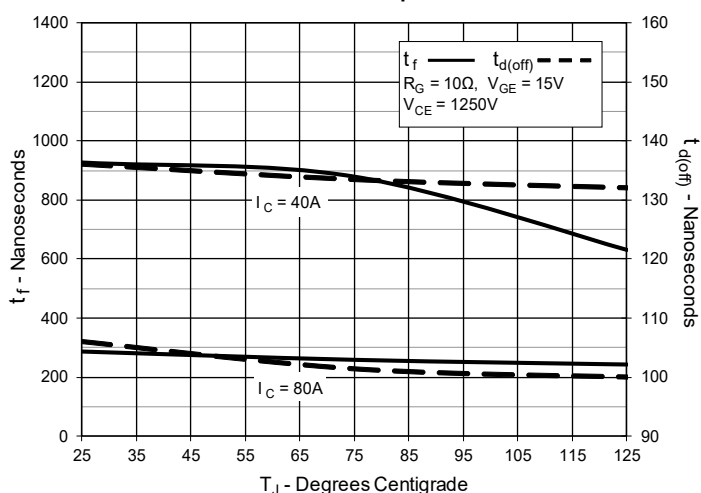


Fig. 16. Resistive Turn-off Switching Times vs. Collector Current

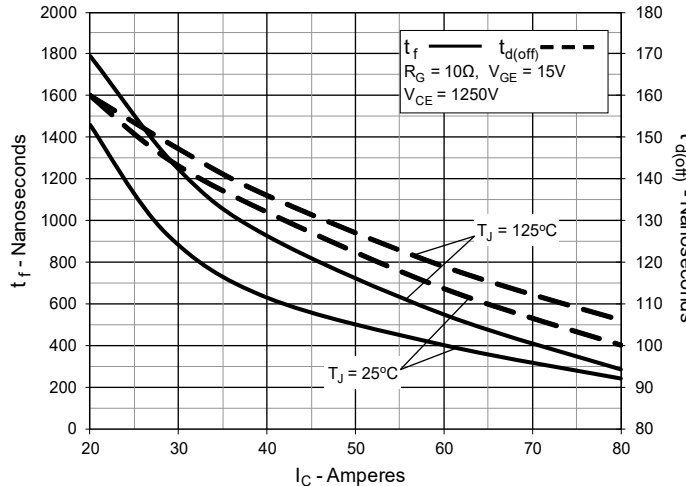
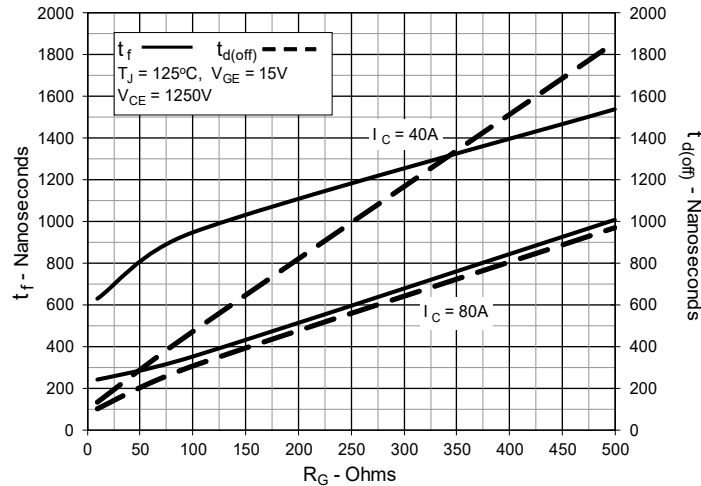
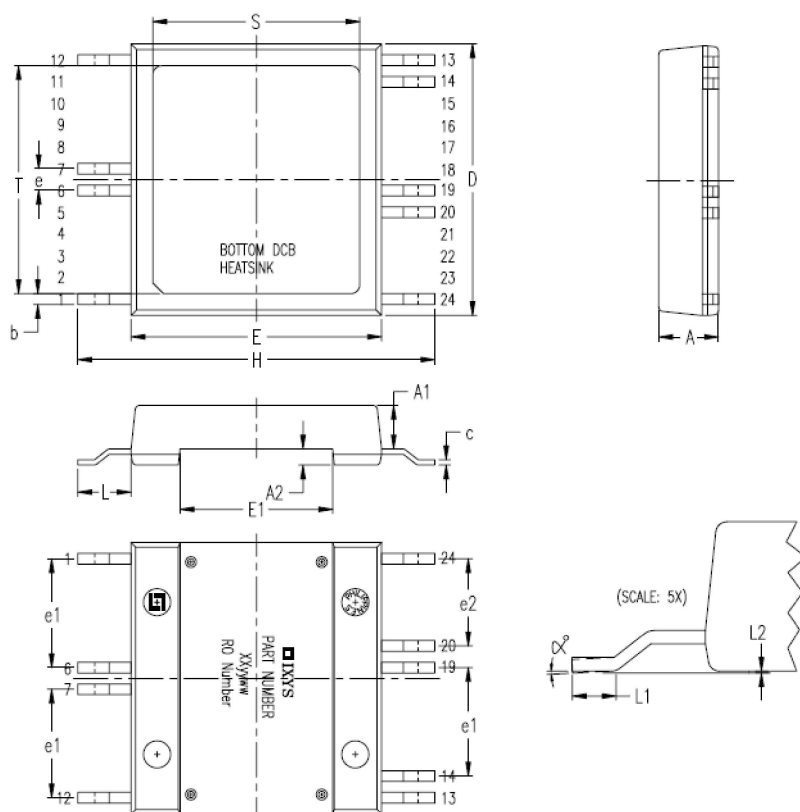


Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance



Package Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.209	.224	5.30	5.70
A1	.154	.161	3.90	4.10
A2	.055	.063	1.40	1.60
b	.035	.045	0.90	1.15
c	.018	.026	0.45	0.65
D	.976	.994	24.80	25.25
E	.898	.915	22.80	23.25
E1	.543	.559	13.80	14.20
e	.079 BSC		2.00 BSC	
e1	.394 BSC		10.00 BSC	
e2	.315 BSC		8.00 BSC	
H	1.272	1.311	32.30	33.30
L	.181	.209	4.60	5.30
L1	.051	.067	1.30	1.70
L2	.000	.006	0.00	0.15
S	.736	.760	18.70	19.30
T	.815	.839	20.70	21.30
α	0	4°	0	4°